



2SK4177

N-Channel Power MOSFET 1500V, 2A, 13Ω, TO-263-2L

ON Semiconductor®

http://onsemi.com

Features

- ON-resistance $R_{DS(on)}=10\Omega$ (typ.)
- Input capacitance $C_{iss}=380pF$ (typ.)
- 10V drive

Specifications

Absolute Maximum Ratings at $T_a=25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		1500	V
Gate-to-Source Voltage	V_{GSS}		± 20	V
Drain Current (DC)	I_D		2	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	4	A
Allowable Power Dissipation	P_D	$T_c = 25^\circ C$	80	W
Channel Temperature	T_{ch}		150	$^\circ C$
Storage Temperature	T_{stg}		-55 to +150	$^\circ C$
Avalanche Energy (Single Pulse) *1	E_{AS}		41	mJ
Avalanche Current *2	I_{AV}		2	A

Note : *1 $V_{DD}=50V$, $L=20mH$, $I_{AV}=2A$ (Fig.1)

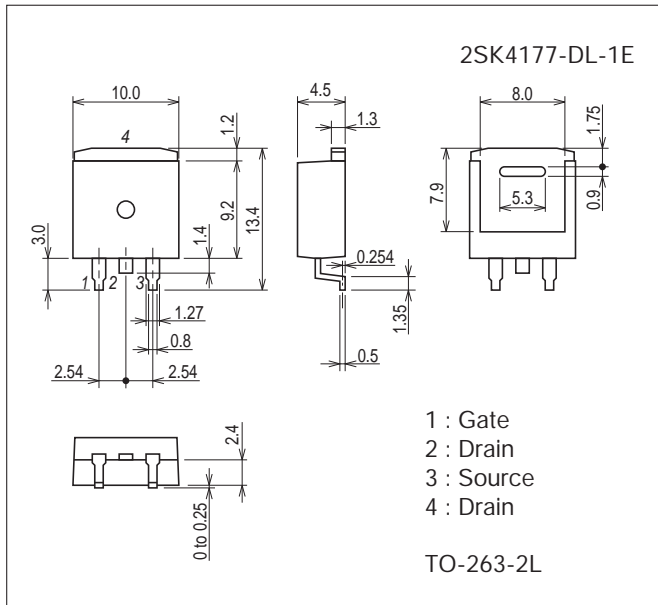
*2 $L \leq 20mH$, single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

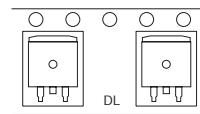
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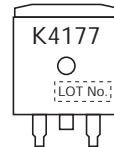
Product & Package Information

- Package : TO-263-2L
- JEITA, JEDEC : SC-83, TO-263
- Minimum Packing Quantity : 800 pcs./reel

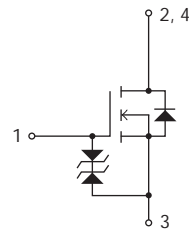
Packing Type: DL



Marking



Electrical Connection



2SK4177

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	1500			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =1200V, V _{GS} =0V			100	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	2.5		3.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} =20V, I _D =1A	0.7	1.4		S
Static Drain-to-Source On-State Resistance	R _{DS(on)}	I _D =1A, V _{GS} =10V		10	13	Ω
Input Capacitance	C _{iss}	V _{DS} =30V, f=1MHz		380		pF
Output Capacitance	C _{oss}				70	pF
Reverse Transfer Capacitance	C _{rss}				40	pF
Turn-ON Delay Time	t _{d(on)}	See Fig.2		12		ns
Rise Time	t _r			37		ns
Turn-OFF Delay Time	t _{d(off)}			152		ns
Fall Time	t _f			59		ns
Total Gate Charge	Q _g	V _{DS} =200V, V _{GS} =10V, I _D =2A		37.5		nC
Gate-to-Source Charge	Q _{gs}			2.7		nC
Gate-to-Drain "Miller" Charge	Q _{gd}			20		nC
Diode Forward Voltage	V _{SD}	I _S =2A, V _{GS} =0V		0.88	1.2	V

Fig.1 Unclamped Inductive Switching Test Circuit

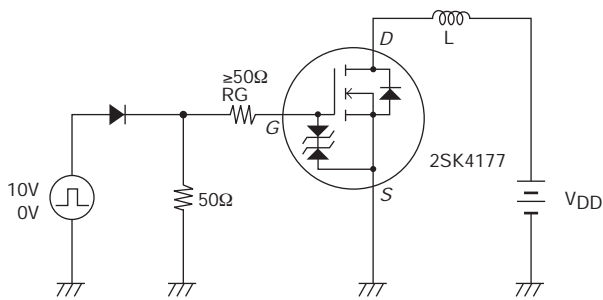
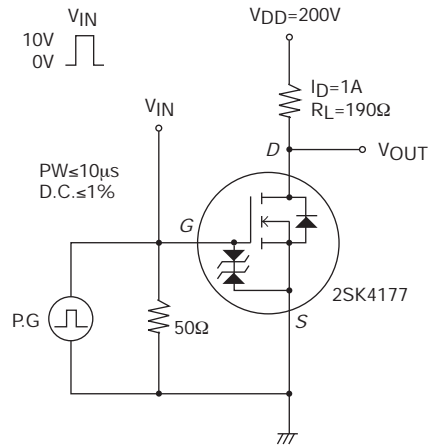
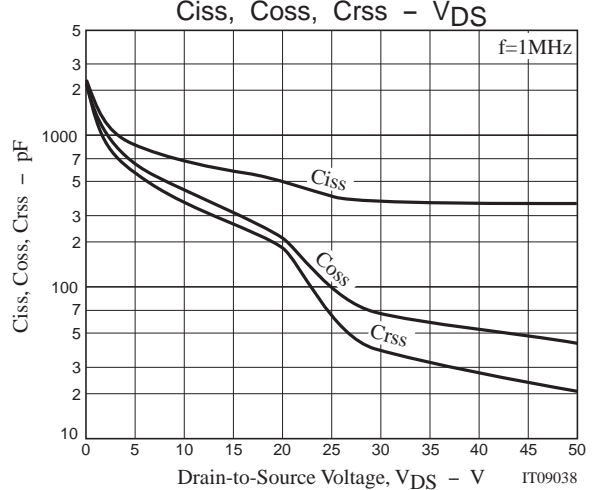
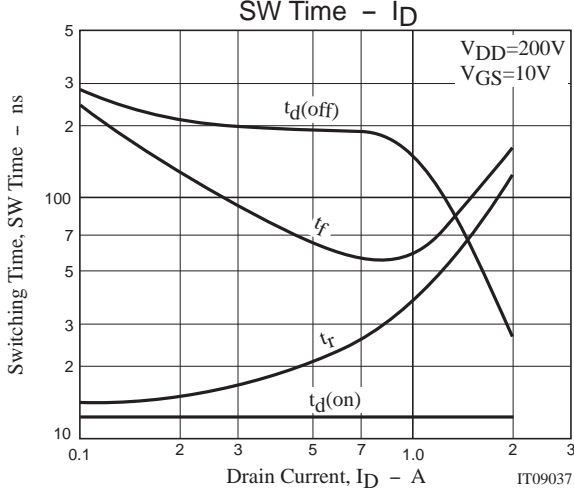
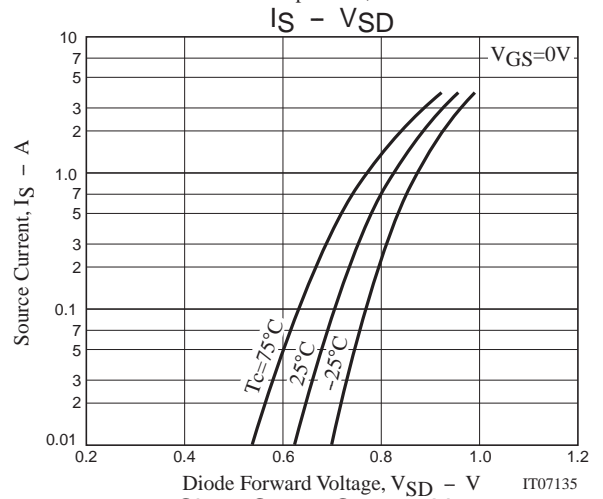
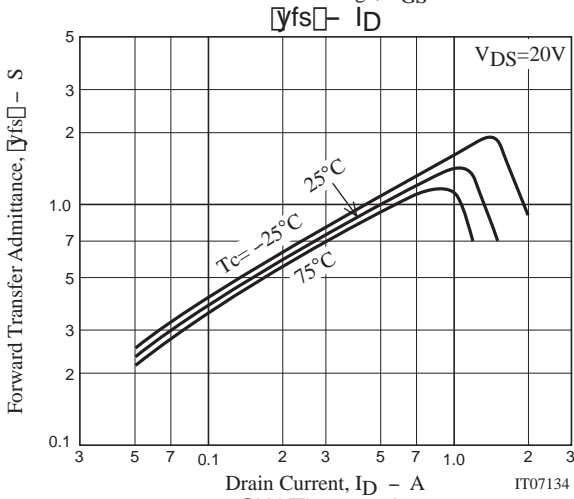
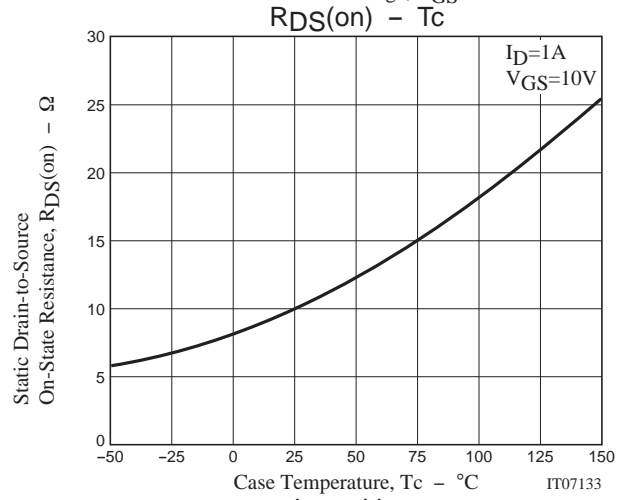
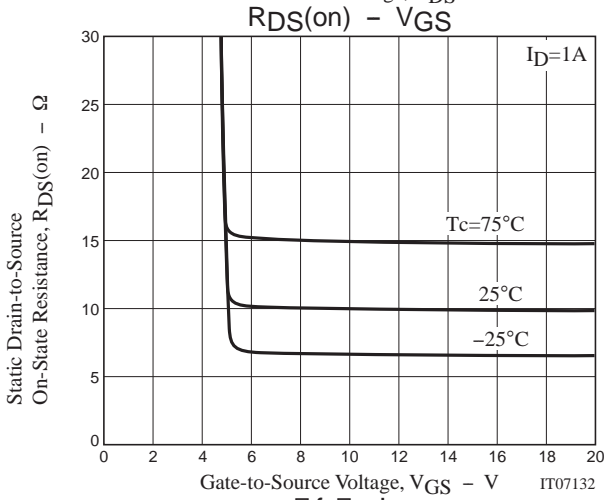
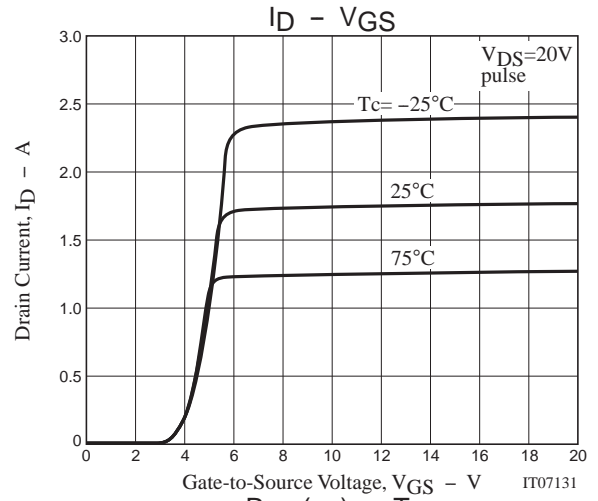
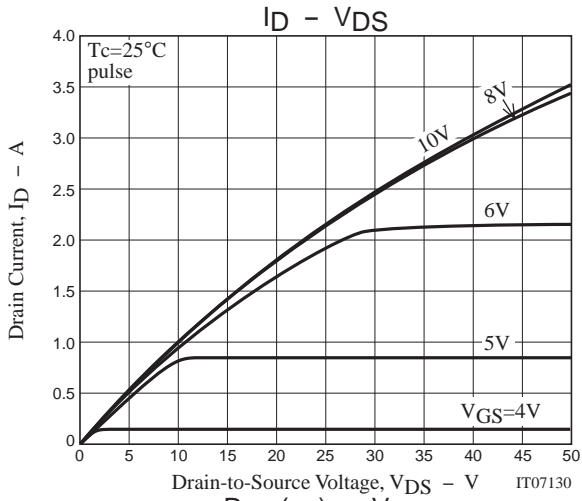


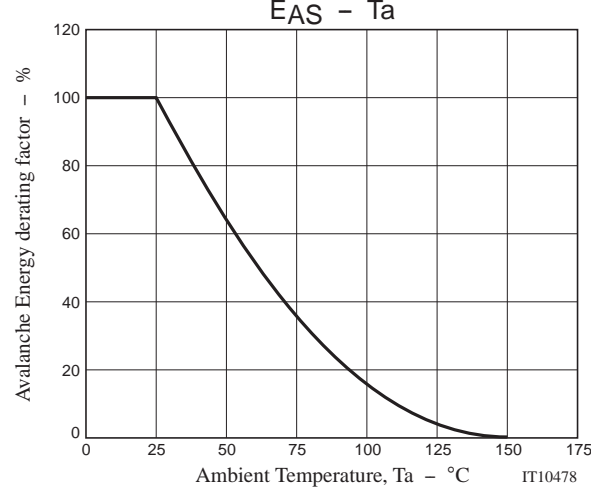
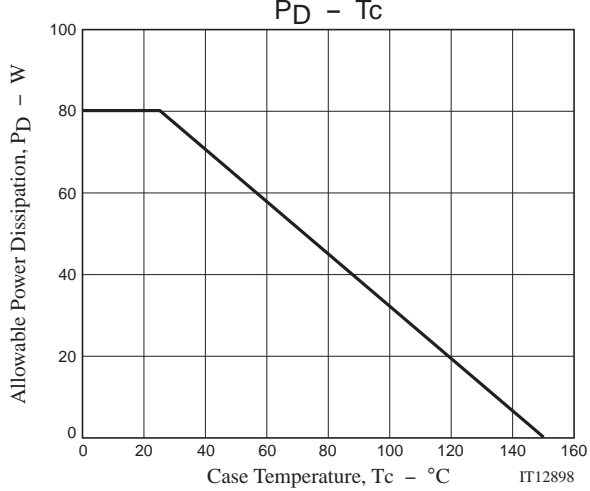
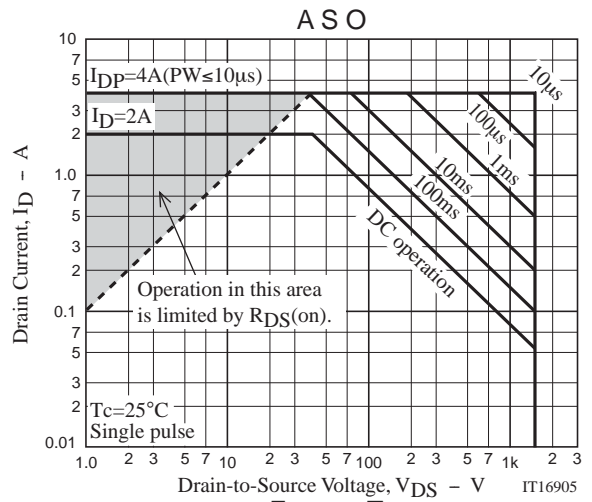
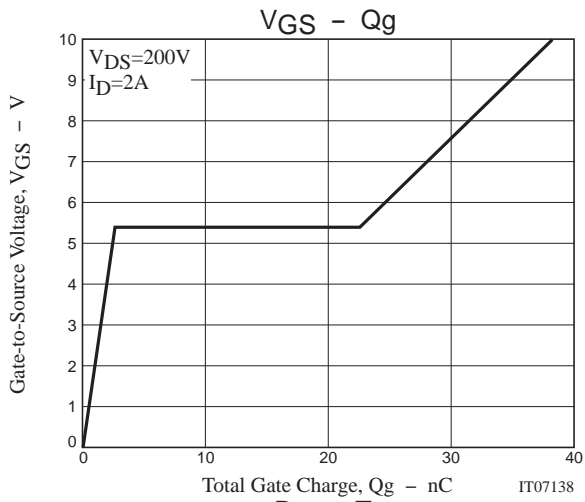
Fig.2 Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
2SK4177-DL-1E	TO-263-2L	800pcs./reel	Pb Free





Taping Specification

2SK4177-DL-1E

1. Packing Format

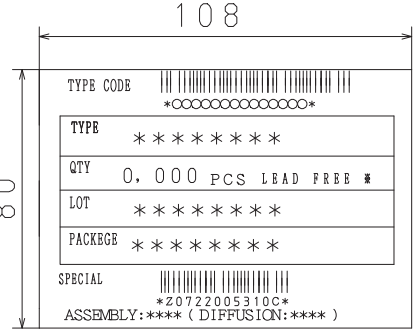
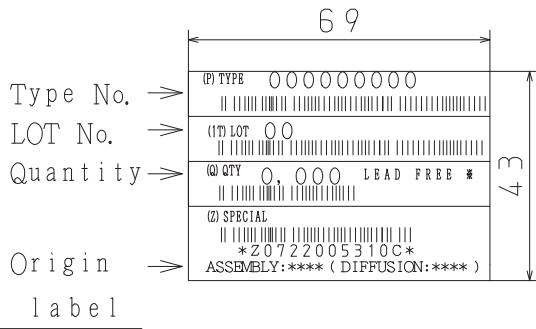
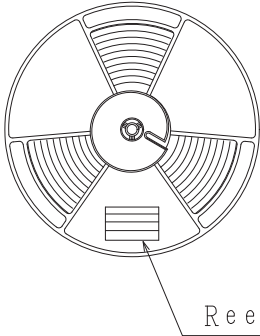
Package Name	Maximum Number of devices contained (pcs)			Packing format	
	Reel	Inner box	Outer box	Inner BOX	Outer BOX
TO-263-2L	800	1600	6400	SPD-0V0011 2 reel contained Dimensions:mm (external) 351×340×68	SPD-0V0009 4 inner boxes contained Dimensions:mm (external) 390×370×318

Reel label, Inner box label (unit:mm)

Outer box label

Packing method

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



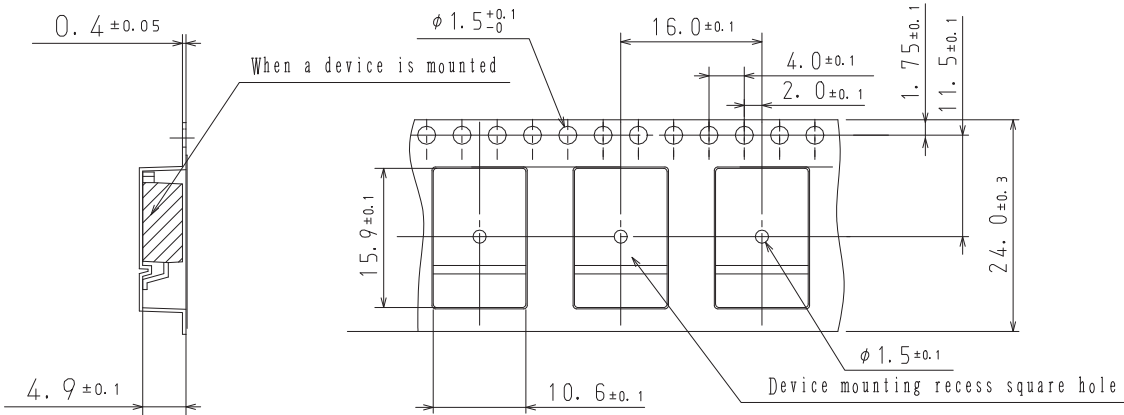
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

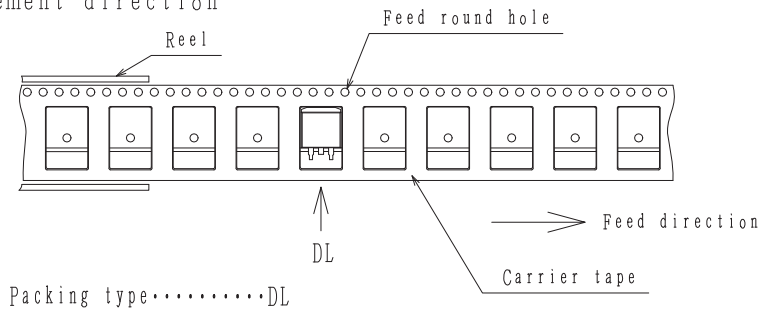
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A

2. Taping configuration

2-1. Carrier tape size (unit:mm)

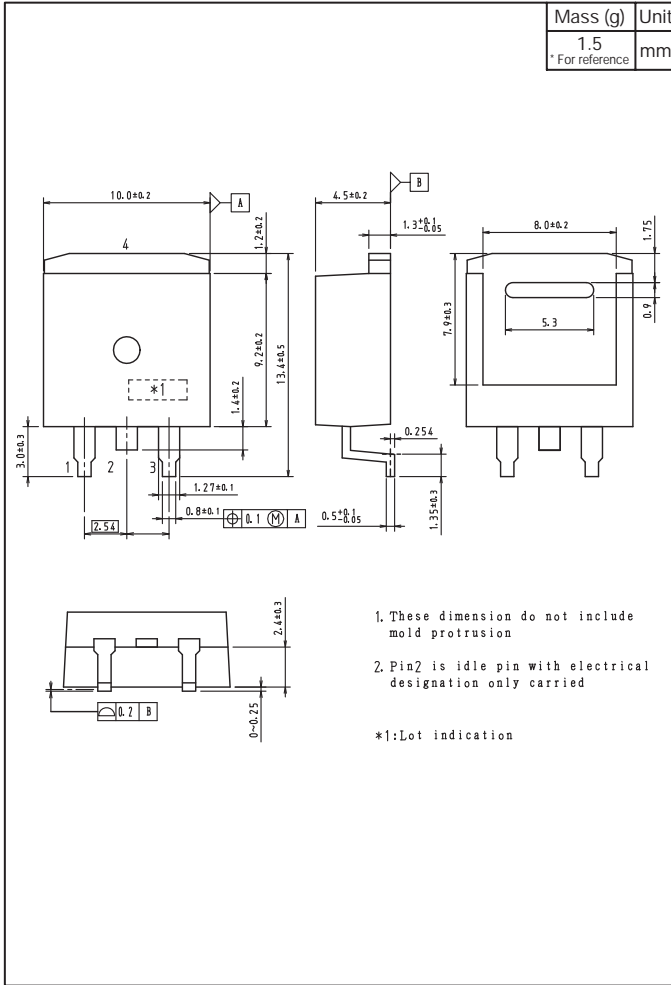


2-2. Device placement direction

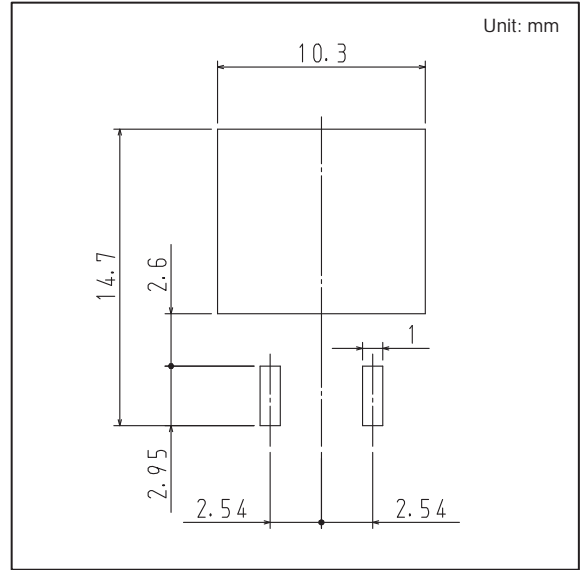


2SK4177

Outline Drawing 2SK4177-DL-1E



Land Pattern Example



Note on usage : Since the 2SK4177 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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